

ON Semiconductor®

2N4401 / MMBT4401 NPN General-Purpose Amplifier

Description

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

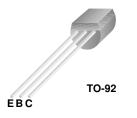


Figure 1. 2N4401 Device Package

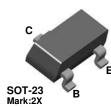


Figure 2. MMBT4401 Device Package

Ordering Information

Part Number	Marking	Package	Packing Method
2N4401BU	2N4401	TO-92 3L	Bulk
2N4401TF	2N4401	TO-92 3L	Tape and Reel
2N4401TFR	2N4401	TO-92 3L	Tape and Reel
2N4401TA	2N4401	TO-92 3L	Ammo
2N4401TAR	2N4401	TO-92 3L	Ammo
MMBT4401	2X	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ι _C	Collector Current - Continuous	600	mA
T _{J,} T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or lowduty cycle operations.

Thermal Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Ma	Unit	
		2N4401 ⁽³⁾	MMBT4401 ⁽⁴⁾	Onit
P _D	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	°C/W

Notes:

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.
4. Device mounted on FR-4 PCB 1.6 inch x 1.6 inch x 0.06 inch.

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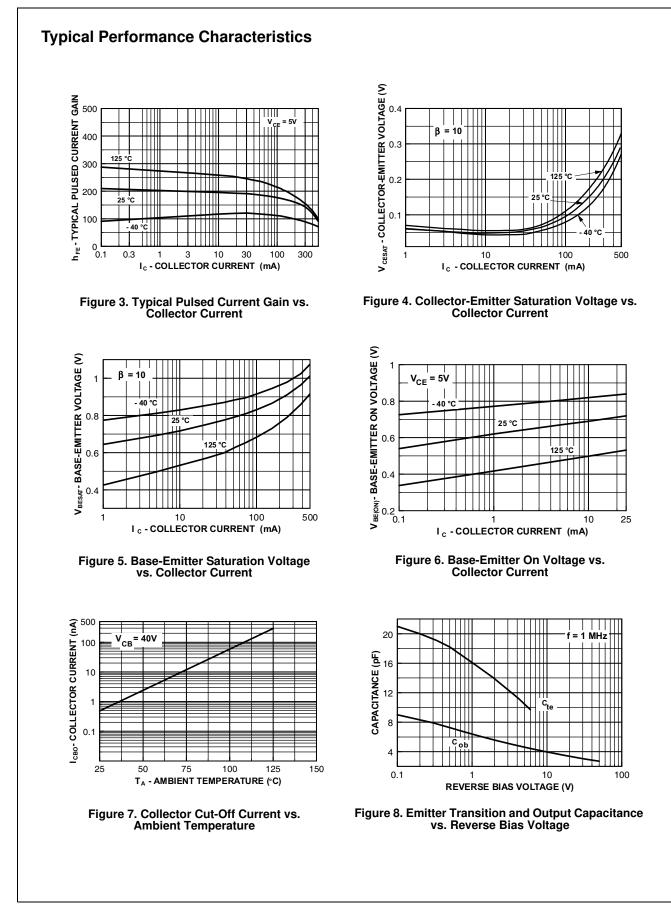
Electrical Characteristics

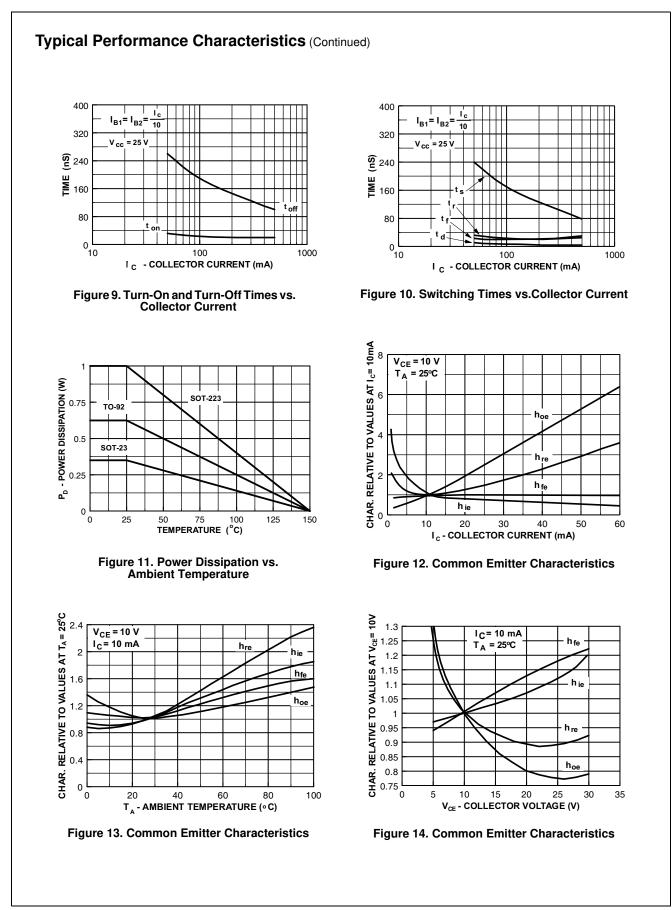
Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

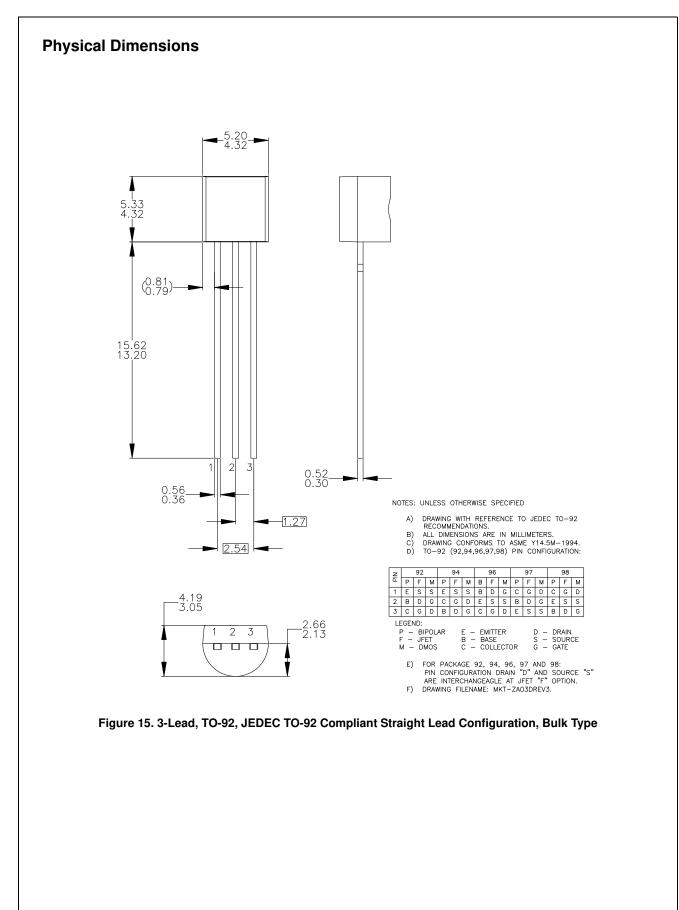
Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage ⁽⁵⁾	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 {\rm mA}, I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 0.1 {\rm mA}, I_{\rm C} = 0$	6.0		V
I _{BL}	Base Cut-Off Current	$V_{CE} = 35 \text{ V}, \text{ V}_{EB} = 0.4 \text{ V}$		0.1	μA
I _{CEX}	Collector Cut-Off Current	$V_{CE} = 35 \text{ V}, \text{ V}_{EB} = 0.4 \text{ V}$		0.1	μA
		$I_{C} = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20		
		I _C = 1.0 mA, V _{CE} = 1.0 V	40		
h _{FE}	DC Current Gain ⁽⁵⁾	I _C = 10 mA, V _{CE} = 1.0 V	80		
		I _C = 150 mA, V _{CE} = 1.0 V	100	300	
		I _C = 500 mA, V _{CE} = 2.0 V	40		
V (aat)	Collector-Emitter Saturation Voltage ⁽⁵⁾	I _C = 150 mA, I _B = 15 mA		0.40	- V
V _{CE} (sat)		I _C = 500 mA, I _B = 50 mA		0.75	
V (aat)	Base-Emitter Saturation Voltage ⁽⁵⁾	I _C = 150 mA, I _B = 15 mA	0.75	0.95	- V
V _{BE} (sat)		I _C = 500 mA, I _B = 50 mA		1.20	
f _T	Current Gain - Bandwidth Product	$I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	250		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0,$ f = 140 kHz		6.5	pF
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		30	pF
h _{ie}	Input Impedance	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	1.0	15.0	kΩ
h _{re}	Voltage Feedback Ratio	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	0.1	8.0	x10 ⁻⁴
h _{fe}	Small-Signal Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	40	500	
h _{oe}	Output Admittance	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	1.0	30	μmho
t _d	Delay Time	V _{CC} = 30 V, V _{EB} = 2 V,		15	ns
t _r	Rise Time	$I_{\rm C} = 150 \text{ mA}, I_{\rm B1} = 15 \text{ mA}$		20	ns
t _s	Storage Time	V _{CC} = 30 V, I _C = 150 mA,		225	ns
t _f	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

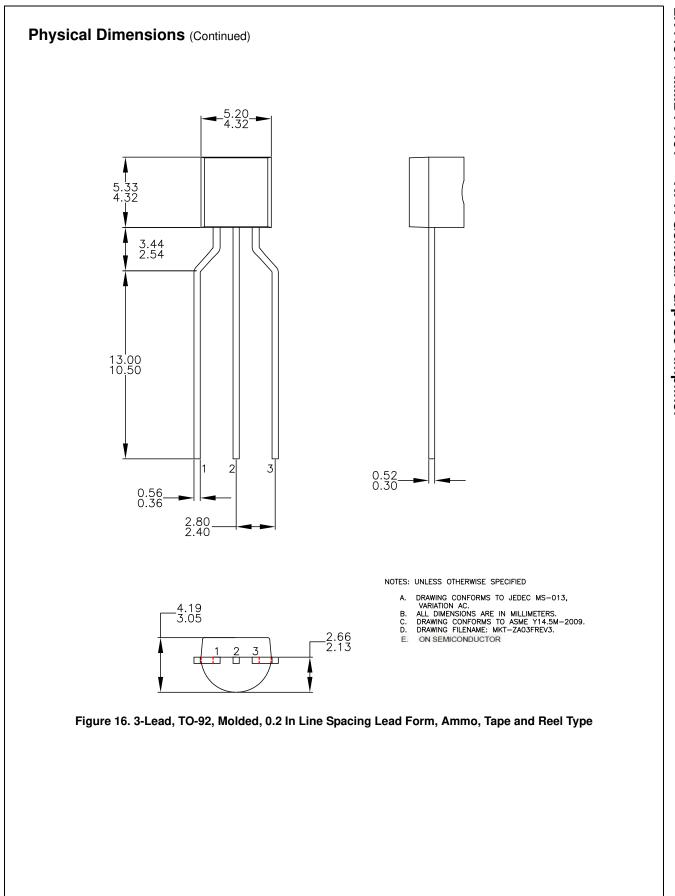
Note:

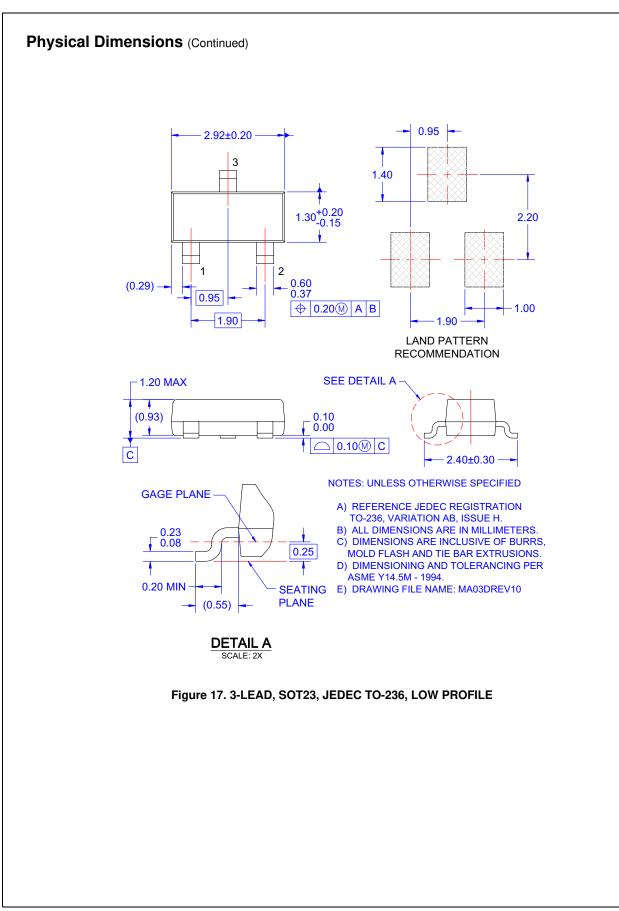
5. Pulse test: pulse width \leq 300 $\mu s,$ duty cycle \leq 2.0%.











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